
Daftar Lagu Lagu Nostalgia Pop Indonesia Tahun 90.rarbfdcm

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1. Field of the Invention This invention relates to a semiconductor device.
2. Description of the Related Art With the recent progress in MOS LSI (large-scale integrated circuit) technologies, the miniaturization of MOS transistors and the like for forming LSIs has proceeded so that the operation of

the MOS transistors becomes a serious problem. The present inventors have found the following. FIG. 10A shows a MOS field effect transistor of a known example. FIG. 10B shows a semiconductor substrate having the MOS field effect transistor formed thereon. Referring to FIGS. 10A and 10B, a region 1001 is a source region and a region 1002 is a drain region. A channel region 1003 is formed between the source region 1001 and the drain region 1002. A gate electrode 1004 is formed above the channel region 1003 with a gate insulating film 1005 interposed therebetween. An impurity layer 1006 is formed in the source region 1001 and the drain region 1002 so that the impurity concentration of the impurity layer 1006 is higher than that of the source region 1001 and the drain region 1002. An impurity layer 1007 is formed on a surface of the semiconductor substrate 1002 between the drain region 1002 and the channel region 1003. In the above known example, when the impurity layer 1006 is formed by ion implantation in the source region 1001 and the drain region 1002, the impurity ions implanted are diffused by the subsequent heat treatment so that the impurity layer

1007 is formed between 2d92ce491b